Preferred Device

Sensitive Gate Triacs

Silicon Bidirectional Thyristors

Designed for high volume, low cost, industrial and consumer applications such as motor control; process control; temperature, light and speed control.

Features

- Small Size Surface Mount DPAK Package
- Passivated Die for Reliability and Uniformity
- Four–Quadrant Triggering
- Blocking Voltage to 600 V
- On–State Current Rating of 4.0 Amperes RMS at 93°C
- Low Level Triggering and Holding Characteristics
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Human Body Model, 3B > 8000 V
 Machine Model, C > 400 V
- Pb-Free Packages are Available

MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) $(T_J = -40 \text{ to } 110^{\circ}\text{C}, \text{ Sine Wave}, 50 \text{ to } 60 \text{ Hz}, \text{ Gate Open})$	V _{DRM,} V _{RRM}	600	V
On–State RMS Current (Full Cycle Sine Wave, 60 Hz, T _C = 93°C)	I _{T(RMS)}	4.0	Α
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, T _J = 110°C)	I _{TSM}	40	Α
Circuit Fusing Consideration (t = 8.3 msec)	I ² t	6.6	A ² sec
Peak Gate Power (Pulse Width ≤ 10 μsec, T _C = 93°C)	P _{GM}	0.5	W
Average Gate Power (t = 8.3 msec, T _C = 93°C)	P _{G(AV)}	0.1	W
Peak Gate Current (Pulse Width ≤ 10 μsec, T _C = 93°C)	I _{GM}	0.2	Α
Peak Gate Voltage (Pulse Width \leq 10 µsec, T _C = 93°C)	V_{GM}	5.0	V
Operating Junction Temperature Range	TJ	-40 to 110	°C
Storage Temperature Range	T _{stg}	-40 to 150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

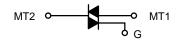
 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the device are exceeded.



ON Semiconductor®

http://onsemi.com

TRIACS 4.0 AMPERES RMS 600 – 800 VOLTS



MARKING DIAGRAMS

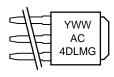


DPAK CASE 369C STYLE 6





DPAK-3 CASE 369D STYLE 6



Y = Year
WW = Work Week
AC4DLM = Device Code
G = Pb-Free Package

PIN ASSIGNMENT			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance - Junction-to-Case - Junction-to-Ambient - Junction-to-Ambient (Note 2)	R _θ JC R _θ JA R _θ JA	3.5 88 80	°C/W
Maximum Lead Temperature for Soldering Purposes (Note 3)	T _L	260	°C

ELECTRICAL CHARACTERISTICS /T

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Peak Repetitive Blocking Current $(V_D = Rated \ V_{DRM}, \ V_{RRM}; \ Gate \ Open)$ $T_J = 25^{\circ}C$ $T_J = 110^{\circ}C$	I XI XIVI		_ _	0.01 2.0	mA
ON CHARACTERISTICS					
Peak On–State Voltage (Note 4) – (I _{TM} = ±6.0 A)	V_{TM}	_	1.3	1.6	V
Gate Trigger Current (Continuous dc) (V_D = 12 V, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	Івт	- - - -	1.8 2.1 2.4 4.2	3.0 3.0 3.0 5.0	mA
Gate Trigger Voltage (Continuous dc) (V_D = 12 V, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	V _{GT}	0.5 0.5 0.5 0.5	0.62 0.57 0.65 0.74	1.3 1.3 1.3 1.3	V
Gate Non–Trigger Voltage $(V_D = 12 \text{ V}, R_L = 100 \Omega, T_J = 110^{\circ}\text{C})$ MT2(+), G(+); MT2(+), G(-); MT2(-), G(-); MT2(-), G(+)	$V_{\sf GD}$	0.1	0.4	_	V
Holding Current $(V_D = 12 \text{ V}, \text{ Gate Open, Initiating Current} = \pm 200 \text{ mA})$	I _H	-	1.5	15	mA
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	IL	- - -	1.75 5.2 2.1 2.2	10 10 10 10	mA
DYNAMIC CHARACTERISTICS					
Rate of Change of Commutating Current (V _D = 200 V, I _{TM} = 1.8 A, Commutating dv/dt = 1.0 V/ μ sec, T _J = 110°C, f = 250 Hz, CL = 5.0 μ fd, LL = 80 mH, RS = 56 Ω , CS = 0.03 μ fd) With snubber see Figure 11	di/dt(c)	-	3.0	-	A/ms
Critical Rate of Rise of Off–State Voltage $(V_D=0.67~X~Rated~V_{DRM},~Exponential~Waveform,~Gate~Open,~T_J=110^{\circ}C)$	dv/dt	10	-	-	V/μs

These ratings are applicable when surface mounted on the minimum pad sizes recommended.
 1/8" from case for 10 seconds.

ORDERING INFORMATION

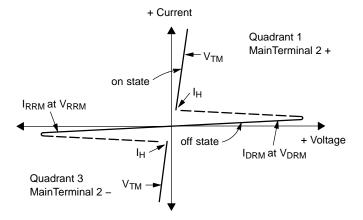
Device	Package Type	Package	Shipping [†]
MAC4DLM-001	DPAK-3	369D	75 Units / Rail
MAC4DLM-001G	DPAK-3 (Pb-Free)	369D	75 Units / Rail
MAC4DLMT4	DPAK	369C	2500 / Tape & Reel
MAC4DLMT4G	DPAK (Pb-Free)	369C	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

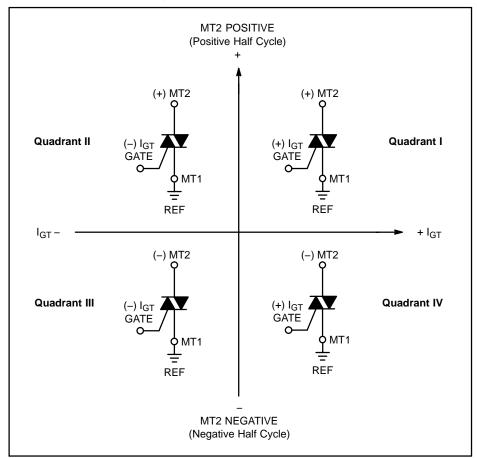
^{4.} Pulse Test: Pulse Width \leq 2.0 msec, Duty Cycle \leq 2%.

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off–State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off–State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On-State Voltage
I _H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

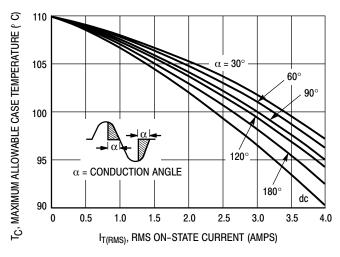


Figure 1. RMS Current Derating

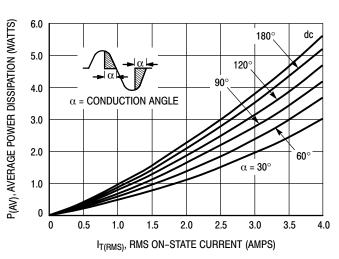


Figure 2. On-State Power Dissipation

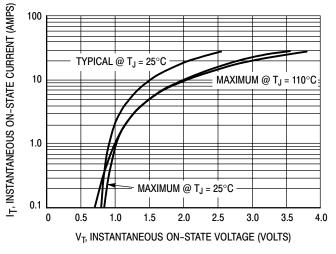


Figure 3. On-State Characteristics

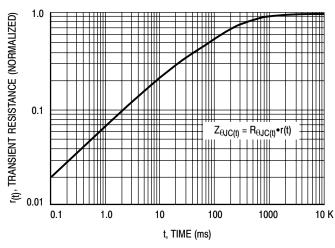


Figure 4. Transient Thermal Response

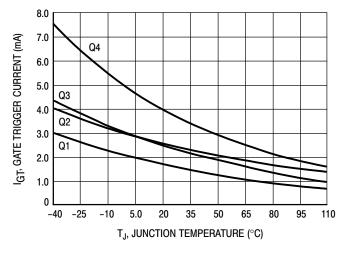


Figure 5. Typical Gate Trigger Current versus
Junction Temperature

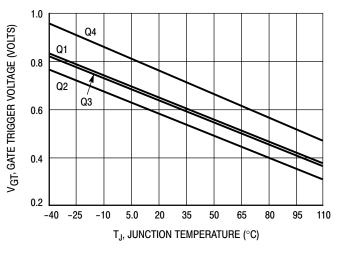
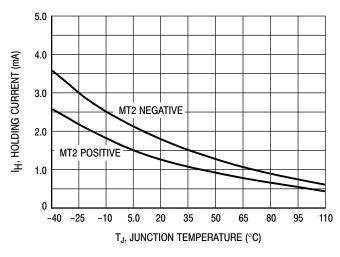


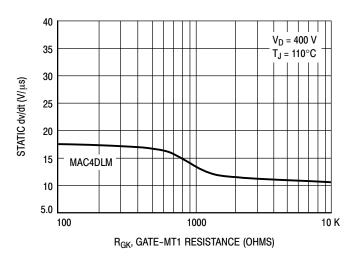
Figure 6. Typical Gate Trigger Voltage versus
Junction Temperature



12 10 IL, LATCHING CURRENT (mA) 8.0 Q2 6.0 4.0 2.0 0 -40 -25 -10 5.0 20 65 80 95 110 35 50 T_J, JUNCTION TEMPERATURE (°C)

Figure 7. Typical Holding Current versus Junction Temperature

Figure 8. Typical Latching Current versus Junction Temperature



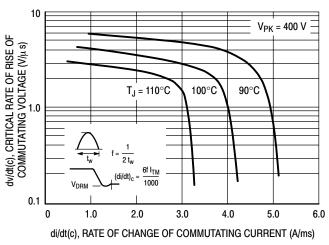
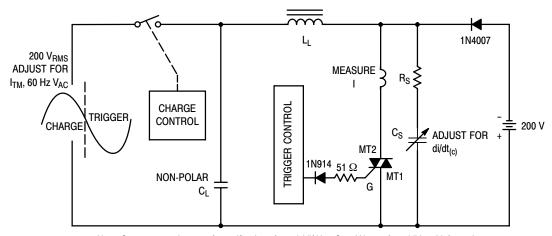


Figure 9. Minimum Exponential Static dv/dt versus Gate-MT1 Resistance

Figure 10. Critical Rate of Rise of Commutating Voltage

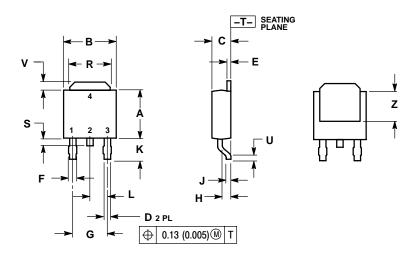


Note: Component values are for verification of rated (di/dt)_c. See AN1048 for additional information.

Figure 11. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)_c

PACKAGE DIMENSIONS

DPAK CASE 369C **ISSUE O**

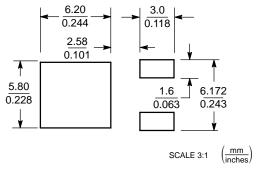


- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.22
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC		4.58	BSC
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29	BSC
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020		0.51	
V	0.035	0.050	0.89	1.27
Z	0.155		3.93	

STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2

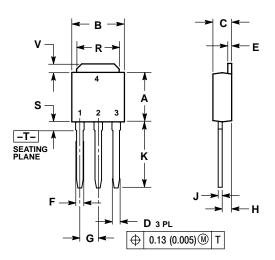
SOLDERING FOOTPRINT*

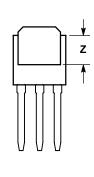


^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

DPAK-3 CASE 369D-01 ISSUE B





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- . CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	BSC	2.29 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155		3.93	

STYLE 6: PIN 1. MT1

2. MT2

3. GATE 4. MT2

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